Intel - EP1S30F780C5 Datasheet





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Details

Product Status	Obsolete
Number of LABs/CLBs	3247
Number of Logic Elements/Cells	32470
Total RAM Bits	3317184
Number of I/O	597
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	780-BBGA, FCBGA
Supplier Device Package	780-FBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1s30f780c5

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1. Introduction

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Introduction

The Stratix[®] family of FPGAs is based on a 1.5-V, 0.13-µm, all-layer copper SRAM process, with densities of up to 79,040 logic elements (LEs) and up to 7.5 Mbits of RAM. Stratix devices offer up to 22 digital signal processing (DSP) blocks with up to 176 (9-bit × 9-bit) embedded multipliers, optimized for DSP applications that enable efficient implementation of high-performance filters and multipliers. Stratix devices support various I/O standards and also offer a complete clock management solution with its hierarchical clock structure with up to 420-MHz performance and up to 12 phase-locked loops (PLLs).

The following shows the main sections in the Stratix Device Family Data Sheet:

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Features

The Stratix family offers the following features:

- 10,570 to 79,040 LEs; see Table 1–1
- Up to 7,427,520 RAM bits (928,440 bytes) available without reducing logic resources
- TriMatrix[™] memory consisting of three RAM block sizes to implement true dual-port memory and first-in first-out (FIFO) buffers
- High-speed DSP blocks provide dedicated implementation of multipliers (faster than 300 MHz), multiply-accumulate functions, and finite impulse response (FIR) filters
- Up to 16 global clocks with 22 clocking resources per device region
- Up to 12 PLLs (four enhanced PLLs and eight fast PLLs) per device provide spread spectrum, programmable bandwidth, clock switchover, real-time PLL reconfiguration, and advanced multiplication and phase shifting
- Support for numerous single-ended and differential I/O standards
- High-speed differential I/O support on up to 116 channels with up to 80 channels optimized for 840 megabits per second (Mbps)
- Support for high-speed networking and communications bus standards including RapidIO, UTOPIA IV, CSIX, HyperTransport™ technology, 10G Ethernet XSBI, SPI-4 Phase 2 (POS-PHY Level 4), and SFI-4
- Differential on-chip termination support for LVDS
- Support for high-speed external memory, including zero bus turnaround (ZBT) SRAM, quad data rate (QDR and QDRII) SRAM, double data rate (DDR) SDRAM, DDR fast cycle RAM (FCRAM), and single data rate (SDR) SDRAM
- Support for 66-MHz PCI (64 and 32 bit) in -6 and faster speed-grade devices, support for 33-MHz PCI (64 and 32 bit) in -8 and faster speed-grade devices
- Support for 133-MHz PCI-X 1.0 in -5 speed-grade devices
- Support for 100-MHz PCI-X 1.0 in -6 and faster speed-grade devices
- Support for 66-MHz PCI-X 1.0 in -7 speed-grade devices
- Support for multiple intellectual property megafunctions from Altera MegaCore[®] functions and Altera Megafunction Partners Program (AMPPSM) megafunctions
- Support for remote configuration updates

Figure 2–11. C4 Interconnect Connections Note (1)



Note to Figure 2–11:

(1) Each C4 interconnect can drive either up or down four rows.

TriMatrix memory architecture can implement pipelined RAM by registering both the input and output signals to the RAM block. All TriMatrix memory block inputs are registered providing synchronous write cycles. In synchronous operation, the memory block generates its own self-timed strobe write enable (WREN) signal derived from the global or regional clock. In contrast, a circuit using asynchronous RAM must generate the RAM WREN signal while ensuring its data and address signals meet setup and hold time specifications relative to the WREN signal. The output registers can be bypassed. Flow-through reading is possible in the simple dual-port mode of M512 and M4K RAM blocks by clocking the read enable and read address registers on the negative clock edge and bypassing the output registers.

Two single-port memory blocks can be implemented in a single M4K block as long as each of the two independent block sizes is equal to or less than half of the M4K block size.

The Quartus II software automatically implements larger memory by combining multiple TriMatrix memory blocks. For example, two 256 × 16-bit RAM blocks can be combined to form a 256 × 32-bit RAM block. Memory performance does not degrade for memory blocks using the maximum number of words available in one memory block. Logical memory blocks using less than the maximum number of words use physical blocks in parallel, eliminating any external control logic that would increase delays. To create a larger high-speed memory block, the Quartus II software automatically combines memory blocks with LE control logic.

Clear Signals

When applied to input registers, the asynchronous clear signal for the TriMatrix embedded memory immediately clears the input registers. However, the output of the memory block does not show the effects until the next clock edge. When applied to output registers, the asynchronous clear signal clears the output registers and the effects are seen immediately.

Parity Bit Support

The memory blocks support a parity bit for each byte. The parity bit, along with internal LE logic, can implement parity checking for error detection to ensure data integrity. You can also use parity-size data words to store user-specified control bits. In the M4K and M-RAM blocks, byte enables are also available for data input masking during write operations.

M512 RAM Block

The M512 RAM block is a simple dual-port memory block and is useful for implementing small FIFO buffers, DSP, and clock domain transfer applications. Each block contains 576 RAM bits (including parity bits). M512 RAM blocks can be configured in the following modes:

- Simple dual-port RAM
- Single-port RAM
- FIFO
- ROM
- Shift register

When configured as RAM or ROM, you can use an initialization file to pre-load the memory contents.

The memory address depths and output widths can be configured as $512 \times 1, 256 \times 2, 128 \times 4, 64 \times 8$ (64×9 bits with parity), and 32×16 (32×18 bits with parity). Mixed-width configurations are also possible, allowing different read and write widths. Table 2–4 summarizes the possible M512 RAM block configurations.

Table 2–4. M512 RAM Block Configurations (Simple Dual-Port RAM)							
Rood Port			V	Vrite Port	t		
Reau Port	512 × 1	256 × 2	128 × 4	64 × 8	32 × 16	64 × 9	32 × 18
512 × 1	\checkmark	\checkmark	~	\checkmark	~		
256 × 2	~	~	~	~	~		
128 × 4	\checkmark	~	~		~		
64 × 8	\checkmark	~		\checkmark			
32 × 16	~	~	~		~		
64 × 9						\checkmark	
32 × 18							~

When the M512 RAM block is configured as a shift register block, a shift register of size up to 576 bits is possible.

The M512 RAM block can also be configured to support serializer and deserializer applications. By using the mixed-width support in combination with DDR I/O standards, the block can function as a SERDES to support low-speed serial I/O standards using global or regional clocks. See "I/O Structure" on page 2–104 for details on dedicated SERDES in Stratix devices.

M-RAM Block

The largest TriMatrix memory block, the M-RAM block, is useful for applications where a large volume of data must be stored on-chip. Each block contains 589,824 RAM bits (including parity bits). The M-RAM block can be configured in the following modes:

- True dual-port RAM
- Simple dual-port RAM
- Single-port RAM
- FIFO RAM

You cannot use an initialization file to initialize the contents of a M-RAM block. All M-RAM block contents power up to an undefined value. Only synchronous operation is supported in the M-RAM block, so all inputs are registered. Output registers can be bypassed. The memory address and output width can be configured as $64K \times 8$ (or $64K \times 9$ bits), $32K \times 16$ (or $32K \times 18$ bits), $16K \times 32$ (or $16K \times 36$ bits), $8K \times 64$ (or $8K \times 72$ bits), and $4K \times 128$ (or $4K \times 144$ bits). The $4K \times 128$ configuration is unavailable in true dual-port mode because there are a total of 144 data output drivers in the block. Mixed-width configurations are also possible, allowing different read and write widths. Tables 2–8 and 2–9 summarize the possible M-RAM block configurations:

Table 2–8. M-RAM Block Configurations (Simple Dual-Port)								
Dood Dort		Write Port						
Read Port64K × 932k		32K × 18	16K × 36	8K × 72	4K × 144			
64K × 9	\checkmark	\checkmark	\checkmark	\checkmark				
32K × 18	\checkmark	\checkmark	\checkmark	~				
16K × 36	\checkmark	\checkmark	\checkmark	~				
8K × 72	\checkmark	 Image: A set of the set of the	\checkmark	~				
4K × 144					\checkmark			



Note to Figure 2–42:

(1) The corner fast PLLs can also be driven through the global or regional clock networks. The global or regional clock input to the fast PLL can be driven by an output from another PLL, a pin-driven global or regional clock, or internallygenerated global signals.

Regional Clock Network

There are four regional clock networks within each quadrant of the Stratix device that are driven by the same dedicated CLK[15..0] input pins or from PLL outputs. From a top view of the silicon, RCLK[0..3] are in the top left quadrant, RCLK[8..11] are in the top-right quadrant, RCLK[4..7] are in the bottom-left quadrant, and RCLK[12..15] are in the bottom-right quadrant. The regional clock networks only pertain to the quadrant they drive into. The regional clock networks provide the lowest clock delay and skew for logic contained within a single quadrant. RCLK cannot be driven by internal logic. The CLK clock pins symmetrically drive the RCLK networks within a particular quadrant, as shown in Figure 2–43. See Figures 2–50 and 2–51 for RCLK connections from PLLs and CLK pins.



IOE clocks have horizontal and vertical block regions that are clocked by eight I/O clock signals chosen from the 22 quadrant or half-quadrant clock resources. Figures 2–47 and 2–48 show the quadrant and halfquadrant relationship to the I/O clock regions, respectively. The vertical regions (column pins) have less clock delay than the horizontal regions (row pins).



Figure 2–50 shows the global and regional clocking from the PLL outputs and the CLK pins.

Notes to Figure 2–50:

- (1) PLLs 1 to 4 and 7 to 10 are fast PLLs. PLLs 5, 6, 11, and 12 are enhanced PLLs.
- (2) The global or regional clocks in a fast PLL's quadrant can drive the fast PLL input. A pin or other PLL must drive the global or regional source. The source cannot be driven by internally generated logic before driving the fast PLL.

Figure 2–51 shows the global and regional clocking from enhanced PLL outputs and top CLK pins.

The pllenable pin is a dedicated pin that enables/disables PLLs. When the pllenable pin is low, the clock output ports are driven by GND and all the PLLs go out of lock. When the pllenable pin goes high again, the PLLs relock and resynchronize to the input clocks. You can choose which PLLs are controlled by the pllenable signal by connecting the pllenable input port of the altpll megafunction to the common pllenable input pin.

The areset signals are reset/resynchronization inputs for each PLL. The areset signal should be asserted every time the PLL loses lock to guarantee correct phase relationship between the PLL output clocks. Users should include the areset signal in designs if any of the following conditions are true:

- PLL Reconfiguration or Clock switchover enables in the design.
- Phase relationships between output clocks need to be maintained after a loss of lock condition

The device input pins or logic elements (LEs) can drive these input signals. When driven high, the PLL counters will reset, clearing the PLL output and placing the PLL out of lock. The VCO will set back to its nominal setting (~700 MHz). When driven low again, the PLL will resynchronize to its input as it relocks. If the target VCO frequency is below this nominal frequency, then the output frequency will start at a higher value than desired as the PLL locks. If the system cannot tolerate this, the clkena signal can disable the output clocks until the PLL locks.

The pfdena signals control the phase frequency detector (PFD) output with a programmable gate. If you disable the PFD, the VCO operates at its last set value of control voltage and frequency with some long-term drift to a lower frequency. The system continues running when the PLL goes out of lock or the input clock is disabled. By maintaining the last locked frequency, the system has time to store its current settings before shutting down. You can either use your own control signal or a clkloss status signal to trigger pfdena.

The clkena signals control the enhanced PLL regional and global outputs. Each regional and global output port has its own clkena signal. The clkena signals synchronously disable or enable the clock at the PLL output port by gating the outputs of the *g* and *l* counters. The clkena signals are registered on the falling edge of the counter output clock to enable or disable the clock without glitches. Figure 2–57 shows the waveform example for a PLL clock port enable. The PLL can remain locked independent of the clkena signals since the loop-related counters are not affected. This feature is useful for applications that require a low power or sleep mode. Upon re-enabling, the PLL does not need a

Table 2–27. DQS & DQ Bus Mode Support (Part 2 of 2			1)	
Device	Package	Number of ×8 Groups	Number of ×16 Groups	Number of ×32 Groups
EP1S25	672-pin BGA 672-pin FineLine BGA	16 (3)	8	4
	780-pin FineLine BGA 1,020-pin FineLine BGA	20	8	4
EP1S30	956-pin BGA 780-pin FineLine BGA 1,020-pin FineLine BGA	20	8	4
EP1S40	956-pin BGA 1,020-pin FineLine BGA 1,508-pin FineLine BGA	20	8	4
EP1S60	956-pin BGA 1,020-pin FineLine BGA 1,508-pin FineLine BGA	20	8	4
EP1S80	956-pin BGA 1,508-pin FineLine BGA 1,923-pin FineLine BGA	20	8	4

Notes to Table 2–27:

 See the Selectable I/O Standards in Stratix & Stratix GX Devices chapter in the Stratix Device Handbook, Volume 2 for V_{REF} guidelines.

(2) These packages have six groups in I/O banks 3 and 4 and six groups in I/O banks 7 and 8.

(3) These packages have eight groups in I/O banks 3 and 4 and eight groups in I/O banks 7 and 8.

(4) This package has nine groups in I/O banks 3 and 4 and nine groups in I/O banks 7 and 8.

(5) These packages have three groups in I/O banks 3 and 4 and four groups in I/O banks 7 and 8.

A compensated delay element on each DQS pin automatically aligns input DQS synchronization signals with the data window of their corresponding DQ data signals. The DQS signals drive a local DQS bus in the top and bottom I/O banks. This DQS bus is an additional resource to the I/O clocks and is used to clock DQ input registers with the DQS signal.

Two separate single phase-shifting reference circuits are located on the top and bottom of the Stratix device. Each circuit is driven by a system reference clock through the CLK pins that is the same frequency as the DQS signal. Clock pins CLK [15..12] p feed the phase-shift circuitry on the top of the device and clock pins CLK [7..4] p feed the phase-shift circuitry on the bottom of the device. The phase-shifting reference circuit on the top of the device controls the compensated delay elements for all 10 DQS pins located at the top of the device. The phase-shifting reference circuit on the bottom of the device controls the compensated delay elements for all 10 DQS pins located on the bottom of the device. All 10 delay elements (DQS signals) on either the top or bottom of the device.



Figure 2–70. Stratix I/O Banks Notes (1), (2), (3)

Notes to Figure 2–70:

- (1) Figure 2–70 is a top view of the silicon die. This will correspond to a top-down view for non-flip-chip packages, but will be a reverse view for flip-chip packages.
- (2) Figure 2–70 is a graphic representation only. See the device pin-outs on the web (**www.altera.com**) and the Quartus II software for exact locations.
- (3) Banks 9 through 12 are enhanced PLL external clock output banks.
- (4) If the high-speed differential I/O pins are not used for high-speed differential signaling, they can support all of the I/O standards except HSTL Class I and II, GTL, SSTL-18 Class II, PCI, PCI-X 1.0, and AGP 1×/2×.
- (5) For guidelines for placing single-ended I/O pads next to differential I/O pads, see the *Selectable I/O Standards in Stratix and Stratix GX Devices* chapter in the *Stratix Device Handbook, Volume 2*.

The transmitter external clock output is transmitted on a data channel. The txclk pin for each bank is located in between data transmitter pins. For ×1 clocks (e.g., 622 Mbps, 622 MHz), the high-speed PLL clock bypasses the SERDES to drive the output pins. For half-rate clocks (e.g., 622 Mbps, 311 MHz) or any other even-numbered factor such as 1/4, 1/7, 1/8, or 1/10, the SERDES automatically generates the clock in the Quartus II software.

For systems that require more than four or eight high-speed differential I/O clock domains, a SERDES bypass implementation is possible using IOEs.

Byte Alignment

For high-speed source synchronous interfaces such as POS-PHY 4, XSBI, RapidIO, and HyperTransport technology, the source synchronous clock rate is not a byte- or SERDES-rate multiple of the data rate. Byte alignment is necessary for these protocols since the source synchronous clock does not provide a byte or word boundary since the clock is one half the data rate, not one eighth. The Stratix device's high-speed differential I/O circuitry provides dedicated data realignment circuitry for usercontrolled byte boundary shifting. This simplifies designs while saving LE resources. An input signal to each fast PLL can stall deserializer parallel data outputs by one bit period. You can use an LE-based state machine to signal the shift of receiver byte boundaries until a specified pattern is detected to indicate byte alignment.

Power Sequencing & Hot Socketing

Because Stratix devices can be used in a mixed-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. Therefore, the VCCIO and VCCINT power supplies may be powered in any order.

Although you can power up or down the VCCIO and VCCINT power supplies in any sequence, you should not power down any I/O banks that contain configuration pins while leaving other I/O banks powered on. For power up and power down, all supplies (VCCINT and all VCCIO power planes) must be powered up and down within 100 ms of each other. This prevents I/O pins from driving out.

Signals can be driven into Stratix devices before and during power up without damaging the device. In addition, Stratix devices do not drive out during power up. Once operating conditions are reached and the device is configured, Stratix devices operate as specified by the user. For more information, see *Hot Socketing* in the *Selectable I/O Standards in Stratix & Stratix GX Devices* chapter in the *Stratix Device Handbook, Volume 2.*

Table 4–108.	Stratix I/O S	Standard	Output De	elay Adde	rs for Slo	w Slew R	ate on Ro	w Pins		
1/0.01	1	-5 Spee	d Grade	-6 Spee	-6 Speed Grade		d Grade	-8 Spee	d Grade	11-14
I/U Stand	ara	Min	Max	Min	Max	Min	Max	Min	Max	Unit
LVCMOS	2 mA		1,571		1,650		1,650		1,650	ps
	4 mA		594		624		624		624	ps
	8 mA		208		218		218		218	ps
	12 mA		0		0		0		0	ps
3.3-V LVTTL	4 mA		1,571		1,650		1,650		1,650	ps
	8 mA		1,393		1,463		1,463		1,463	ps
	12 mA		596		626		626		626	ps
	16 mA		562		590		590		590	ps
2.5-V LVTTL	2 mA		2,562		2,690		2,690		2,690	ps
	8 mA		1,343		1,410		1,410		1,410	ps
	12 mA		864		907		907		907	ps
	16 mA		945		992		992		992	ps
1.8-V LVTTL	2 mA		6,306		6,621		6,621		6,621	ps
	8 mA		3,369		3,538		3,538		3,538	ps
	12 mA		2,932		3,079		3,079		3,079	ps
1.5-V LVTTL	2 mA		9,759		10,247		10,247		10,247	ps
	4 mA		6,830		7,172		7,172		7,172	ps
	8 mA		5,699		5,984		5,984		5,984	ps
GTL+			-333		-350		-350		-350	ps
CTT			591		621		621		621	ps
SSTL-3 Class I			267		280		280		280	ps
SSTL-3 Class II			-346		-363		-363		-363	ps
SSTL-2 Class I			481		505		505		505	ps
SSTL-2 Class I	I		-58		-61		-61		-61	ps
SSTL-18 Class	I		2,207		2,317		2,317		2,317	ps
1.5-V HSTL Cla	ass I		1,966		2,064		2,064'		2,064	ps
1.8-V HSTL Cla	ass I		1,208		1,268		1,460		1,720	ps

The scaling factors for column output pin timing in Tables 4–111 to 4–113 are shown in units of time per pF unit of capacitance (ps/pF). Add this delay to the t_{CO} or combinatorial timing path for output or bidirectional pins in addition to the I/O adder delays shown in Tables 4–103 through 4–108 and the IOE programmable delays in Tables 4–109 and 4–110.

Table 4–111. Output Delay Adder for Loading on LVTTL/LVCMOS Output Buffers Note (1)						
Conditions		Output Pin Adder Delay (ps/pF)				
Parameter	Value	3.3-V LVTTL 2.5-V LVTTL 1.8-V LVTTL 1.5-V LVTTL LVCMOS				
	24mA	15	-	-	-	8
	16mA	25	18	-	-	-
Drive Strength	12mA	30	25	25	Ι	15
Drive Strength	8mA	50	35	40	35	20
	4mA	60	-	-	80	30
	2mA	-	75	120	160	60

Note to Table 4–111:

(1) The timing information in this table is preliminary.

Table 4–112. Output Delay Adder for Loading on SSTL/HSTL Output Buffers Note (1)						
Conditions	Output Pin Adder Delay (ps/pF)					
Conumons	SSTL-3	SSTL-2	SSTL-1.8	1.5-V HSTL		
Class I	25	25	25	25		
Class II	25	20	25	20		

Note to Table 4–112:

(1) The timing information in this table is preliminary.

Table 4–113. Output Delay Adder for Loading on GTL+/GTL/CTT/PCI Output Buffers Note (1)								
Cond	itions	Output Pin Adder Delay (ps/pF)						
Parameter	Value	GTL+	GTL	CTT	PCI	AGP		
VCCIO Voltage	3.3V	18	18	25	20	20		
Level	2.5V	15	18	-	-	-		

Note to Table 4–113:

(1) The timing information in this table is preliminary.

Table 4–123. Stratix Ma.	ximum Outp	out Clock Ra	te (Using I/	0 Pins) for PLL[1,
2, 3, 4] Pins in Wire-Bol	nd Package	s (Part 2 of	f 2)	
I/O Standard	-6 Speed	-7 Speed	-8 Speed	Unit

I/O Standard	Grade	Grade	Grade	Unit
LVDS (2)	400	311	311	MHz
HyperTransport technology (2)	420	400	400	MHz

Notes to Tables 4–120 through 4–123:

- (1) Differential SSTL-2 outputs are only available on column clock pins.
- (2) These parameters are only available on row I/O pins.
- (3) SSTL-2 in maximum drive strength condition. See Table 4–101 on page 4–62 for more information on exact loading conditions for each I/O standard.
- (4) SSTL-2 in minimum drive strength with ≤ 10 pF output load condition.
- (5) SSTL-2 in minimum drive strength with > 10pF output load condition.
- (6) Differential SSTL-2 outputs are only supported on column clock pins.

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Table 4–125. High-Speed I/O Specifications for Flip-Chip Packages (Part 3 of 4) Notes (1), (2)														
Symbol	Conditions	-5 Speed Grade			-6 Speed Grade			-7 Speed Grade			-8 Speed Grade			.
		Min	Тур	Max	- Unit									
SW	PCML (<i>J</i> = 4, 7, 8, 10)	750			750			800			800			ps
	PCML $(J = 2)$	900			900			1,200			1,200			ps
	PCML $(J = 1)$	1,500			1,500			1,700			1,700			ps
	LVDS and LVPECL $(J = 1)$	500			500			550			550			ps
	LVDS, LVPECL, HyperTransport technology (<i>J</i> = 2 through 10)	440			440			500			500			ps
Input jitter tolerance (peak-to-peak)	All			250			250			250			250	ps
Output jitter (peak-to-peak)	All			160			160			200			200	ps
Output t _{RISE}	LVDS	80	110	120	80	110	120	80	110	120	80	110	120	ps
	HyperTransport technology	110	170	200	110	170	200	120	170	200	120	170	200	ps
	LVPECL	90	130	150	90	130	150	100	135	150	100	135	150	ps
	PCML	80	110	135	80	110	135	80	110	135	80	110	135	ps
Output t _{FALL}	LVDS	80	110	120	80	110	120	80	110	120	80	110	120	ps
	HyperTransport technology	110	170	200	110	170	200	110	170	200	110	170	200	ps
	LVPECL	90	130	160	90	130	160	100	135	160	100	135	160	ps
	PCML	105	140	175	105	140	175	110	145	175	110	145	175	ps

process and operating conditions. Run the timing analyzer in the Quartus II software at the fast and slow operating conditions to see the phase shift range that is achieved below these frequencies.

Table 4–135. Stratix DLL Low Frequency Limit for Full Phase Shift							
Phase Shift	Minimum Frequency for Full Phase Shift	Unit					
72°	119	MHz					
90°	149	MHz					



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